

# WP7113PD1BT/BD-P22

Photodiode

### **DESCRIPTION**

• Made with silicon phototransistor chips

#### **FEATURES**

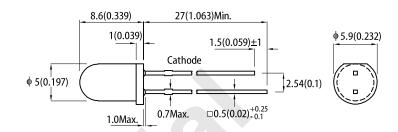
- · Mechanically and spectrally matched to the infrared emitting LED lamp
- Black lens
- RoHS compliant

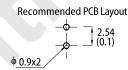
## **APPLICATIONS**

- · Infrared applied systems
- Optoelectronic switches
- · Photodetector control circuits
- · Sensor technology



### **PACKAGE DIMENSIONS**





- Notes:

  1. All dimensions are in millimeters (inches).

  2. Tolerance is ±0.25(0.01") unless otherwise noted.

  3. Lead spacing is measured where the leads emerge from the package.

  4. The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.

# ABSOLUTE MAXIMUM RATINGS at T<sub>A</sub>=25°C

Parameter	Max.Ratings	Units			
Power Dissipation	150	mW			
Operating Temperature	-40 to +85	°C			
Storage Temperature	-40 to +85	°C			
Lead Soldering Temperature [1]	260°C For 3 Seconds				
Lead Soldering Temperature [2]	260°C For 5 Seconds				

<sup>1. 2</sup>mm below package base.
2. 5mm below package base.
3. Relative humidity levels maintained between 40% and 60% in production area are recommended to avoid the build-up of static electricity – Ref JEDEC/JESD625-A and JEDEC/J-STD-033.

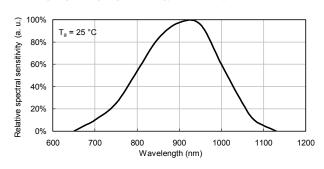


# ELECTRICAL / OPTICAL CHARACTERISTICS at T<sub>A</sub>=25°C

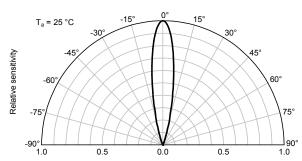
Parameter	Symbol	Min.	Тур.	Max.	Units	Test Conditions
Reverse Break down Voltage	$V_{(BR)R}$	33	170	-	V	$I_R = 100\mu A$ $H = 0mW/cm^2$
Reverse Dark Current	ID <sub>(R)</sub>	-	-	10	nA	$V_R = 10V$ $H = 0mW/cm^2$
Open Circuit Voltage	V <sub>oc</sub>	-	390	-	mV	λ = 940nm H = 5mW/cm <sup>2</sup>
Rise Time	T <sub>R</sub>	-	6	-	nS	$V_R = 10V$ $\lambda = 940$ nm $R_L = 1000\Omega$
Fall Time	T <sub>F</sub>	-	6	-	nS	
Light current	I <sub>S</sub>	1.2	2.0		μА	$V_R = 5V$ $E_e = 0.08 \text{mW/cm}^2$ $\lambda = 940 \text{nm}$
Total Capacitance	Ст	-	5		pF	$V_R = 10V$ $F = 1MHZ$ $H = 0mW/cm^2$
Range of spectral bandwidth	λ <sub>0.1</sub>	670		1070	nm	-
Wavelength of peak sensitivity	$\lambda_{p}$		940	-	nm	-
Angle of half sensitivity	201/2		20	-	deg	-

### **TECHNICAL DATA**

### **RELATIVE SPECTRAL SENSITIVITY vs. WAVELENGTH**



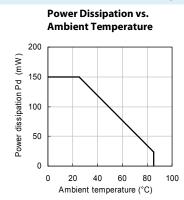
### RELATIVE RADIANT SENSITIVITY vs. ANGULAR DISPLACEMENT

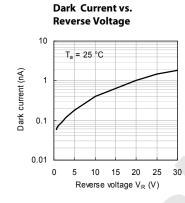




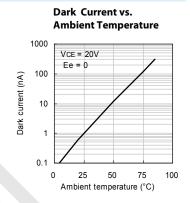
#### **TECHNICAL DATA**

## Light Current vs. Irradiance 1000 V<sub>R</sub>=5V T<sub>a</sub> = 25 °C Light current Is (µA) 100 10 0.1 10 100 1000 Irradiance Ee (µW/cm²)

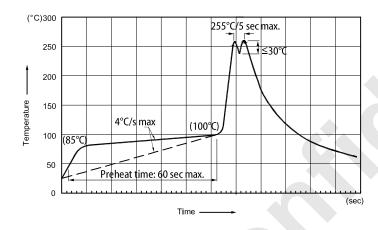




**PHOTODIODE** 



#### **RECOMMENDED WAVE SOLDERING PROFILE**



- attached to the LED pins) prior to immersion in the solder wave with a maximum solder bath temperature of 260°C

  Peak wave soldering temperature between 245°C ~ 255°C for 3 sec (5 sec max).

- 3. Do not apply stress to the epoxy resin while the temperature is above 85°C.

  4. Fixtures should not incur stress on the component when mounting and during soldering process.

  5. SAC 305 solder alloy is recommended.
- 6. No more than one wave soldering pass.

### **PACKING & LABEL SPECIFICATIONS**

